

emitting layer toward a top surface of the light-emitting device has a radiation angle dependence;

a semiconductor layer formed over at least the light-emitting layer, a top surface of the semiconductor layer comprising a roughened surface which is at least partially uncovered and exposed to surrounding atmosphere in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.

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15. (Amended) A semiconductor light-emitting device comprising:

a DBR (Distributed Bragg Reflector) and a light-emitting layer supported by a substrate comprising GaAs, the DBR being located closer to the substrate comprising GaAs than is the light-emitting layer; and

a semiconductor layer formed on the light-emitting layer, and wherein at least part of a top surface of the semiconductor layer is roughened so as to define a roughened surface which is at least partially uncovered and exposed in order to cause light output from the light-emitting device to be diffused upon leaving the top surface of the device; and

wherein no DBR is provided between the light-emitting layer and the semiconductor layer having the top surface that is roughened.

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Please add the following new claims: